

MOS FIELD EFFECT TRANSISTORS

MOS-FELDEFFECT-TRANSISTOREN

| Type Typ | Channel Kanal | Maximum ratings | | ● Grenzdaten | | | | R_I $R_{CE(ON)}^*$ $R_{CE(OFF)} \bullet$ Ω | y_{21} mS | at bei | U_{CE} V | I_C mA | U_{GE} V | C_I pF |
|-------------|------------------|------------------|------------------|---------------|-------------|-----------------|------------------------------|--|----------------|-----------|---------------|-------------|---------------|-------------|
| | | U_{CEM}^* V | U_{GEM}^* V | U_{GC} V | I_C mA | P_{tot} mW | ϑ_J $^{\circ}C$ | | | | | | | |
| KF520 | N | 30 | ± 70 1) | — | 30 | 300 | 175 | $\geq 10^{13}$ | $\geq 0,3$ | | 15 10 | 5 1...3 | 0' | 8 |

1) $U_{CE} = 15 V$